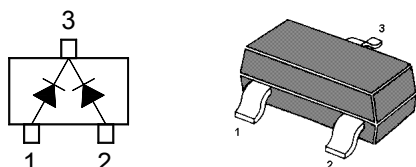


BAV74

Silicon Epitaxial Planar Switching Diode

Applications

Ultra high speed switching application



Marking Code: **A4**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	60	V
Continuous Reverse Voltage	V_R	50	V
Forward Current (DC)	I_{FSM}	215	mA
Single Diode Loaded		125	
Double Diode Loaded	I_{FRM}	450	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5	A
at $t = 1\text{ s}$		1	
at $t = 1\text{ ms}$		4	
at $t = 1\text{ }\mu\text{s}$			
Power Dissipation	P_d	350	mW
Operating Junction Temperature Range	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage			
at $I_F = 1\text{ mA}$	V_F	715	mV
at $I_F = 10\text{ mA}$	V_F	855	mV
at $I_F = 50\text{ mA}$	V_F	1	V
at $I_F = 150\text{ mA}$	V_F	1.25	V
Reverse Current			
at $V_R = 25\text{ V}$	I_R	30	nA
at $V_R = 50\text{ V}$	I_R	0.1	μA
at $V_R = 25\text{ V}, T_J = 150\text{ }^{\circ}\text{C}$	I_R	30	μA
at $V_R = 50\text{ V}, T_J = 150\text{ }^{\circ}\text{C}$	I_R	100	μA
Diode Capacitance	C_d	2	pF
at $V_R = 0, f = 1\text{ MHz}$			
Reverse Recovery Time	t_{rr}	4	ns
at $I_F = I_R = 10\text{ mA}$ to $I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$			

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